

# 2N5401

# **MMBT5401**





# **PNP General Purpose Amplifier**

This device is designed as a general purpose amplifier and switch for applications requiring high voltages.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>CBO</sub>	Collector-Base Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	600	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	W	Units	
	WWW. ON. CO. TW	2N5401	*MMBT5401	
$P_D$	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	. ON CO.	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	150	TON	V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100  \mu A, I_E = 0$	160	N.C.	V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10  \mu A, I_C = 0$	5.0	ov.CO	V
I <sub>CBO</sub> Collector Cutoff Current		$V_{CB} = 120 \text{ V}, I_E = 0$ $V_{CB} = 120 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$	MMI	50 50	nA μA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$	TAN W.	50	nA

#### ON CHARACTERISTICS\*

h <sub>FE</sub>	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$	50 60 50	240	N.COM
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	-4	0.2	V
11/1/4	W.Co. TV	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	N N	0.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		1.0	V
DZ(Gat)	W WITH W	$I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		1.0	00 V

#### SMALL SIGNAL CHARACTERISTICS

SMALL	SIGNAL CHARACTERISTICS				
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz	100	300	MHz
C <sub>obo</sub>	Output Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1.0 MHz		6.0	pF
NF	Noise Figure	$I_C = 250 \mu A$ , $V_{CE} = 5.0 V$ , $R_S = 1.0 kΩ$ , $f = 10 Hz$ to 15.7 kHz	TW	8.0	dB

<sup>\*</sup>Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

**NOTE:** All voltages (V) and currents (A) are negative polarity for PNP transistors.

## **Spice Model**

PNP (Is=21.48f Xti=3 Eg=1.11 Vaf=100 Bf=132.1 Ne=1.375 Is==21.48f Ikf=.1848 Xtb=1.5 Br=3.661 Nc=2 Isc=0 lkr=0 Rc=1.6 Cjc=17.63p Mjc=.5312 Vjc=.75 Fc=.5 Cje=73.39p Mje=.3777 Vje=.75 Tr=1.476n Tf=641.9p ltf=0 Vtf=0 Xtf=0 Rb=10)

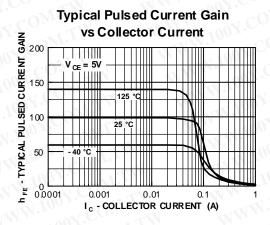
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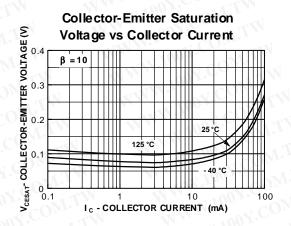
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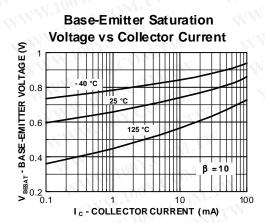
# **PNP General Purpose Amplifier**

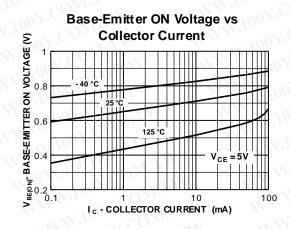
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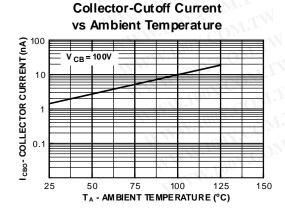
# Typical Characteristics

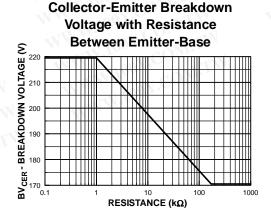












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# **PNP General Purpose Amplifier**

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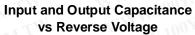
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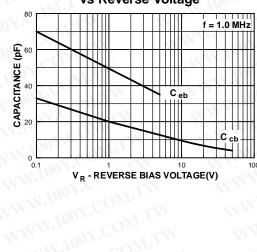
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# Typical Characteristics (continued)

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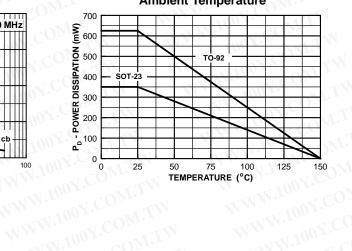
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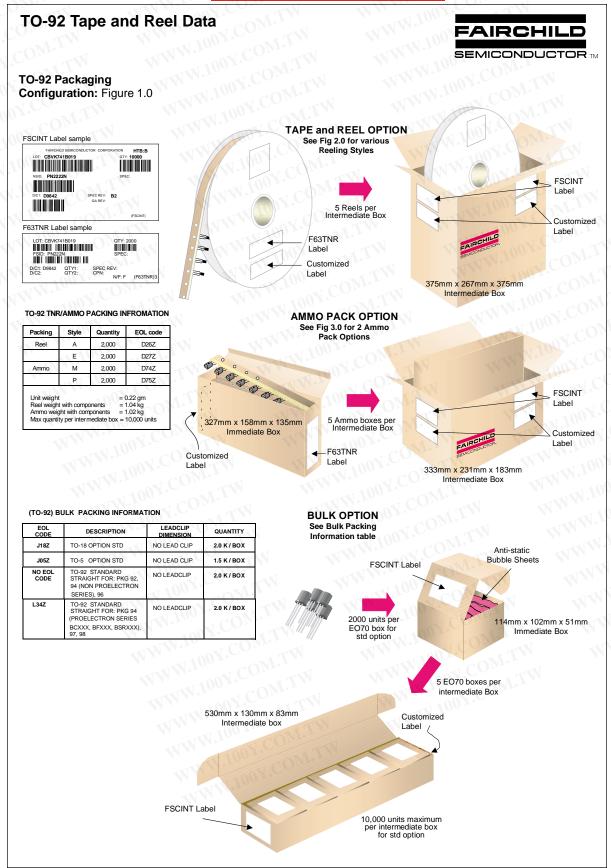
### **Power Dissipation vs Ambient Temperature**



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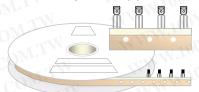


# WWW.100Y.COM.TW TO-92 Tape and Reel Data, continued

## **TO-92 Reeling Style** Configuration: Figure 2.0

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#### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J) 8 8 8 8

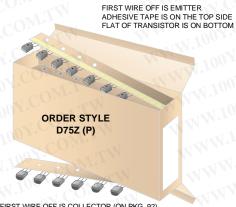
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Style "E", D27Z, D71Z (s/h)

## **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0

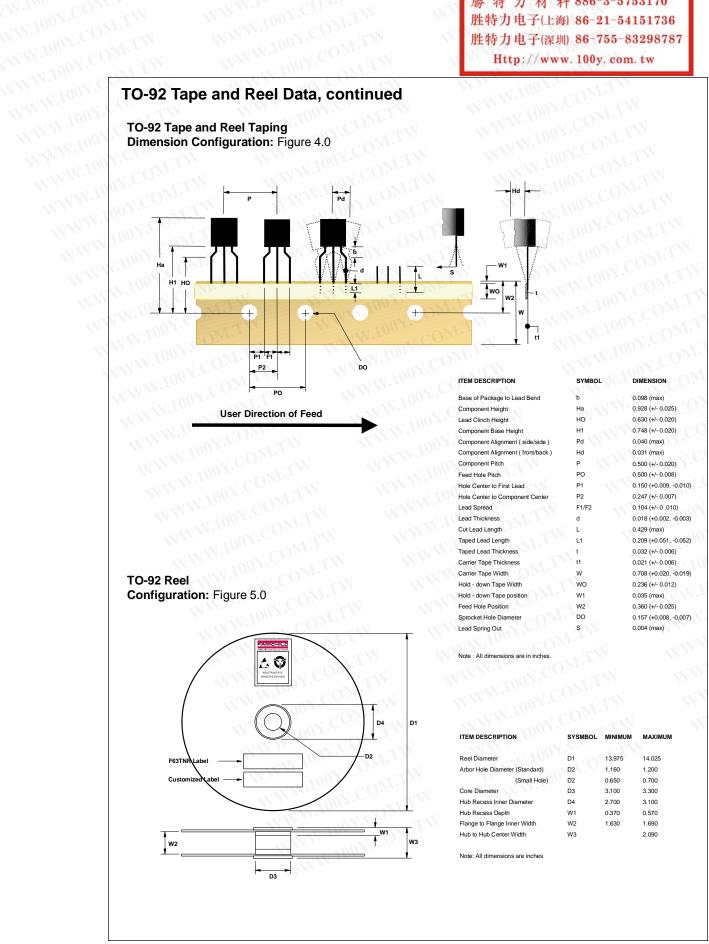


ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

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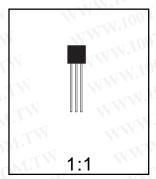


# **TO-92 Package Dimensions**



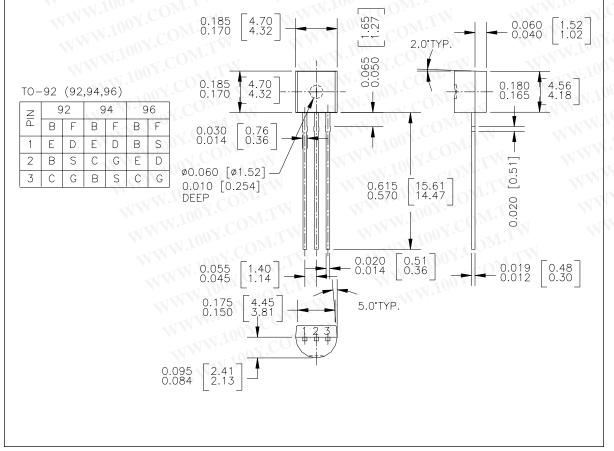
# TO-92 (FS PKG Code 92, 94, 96)

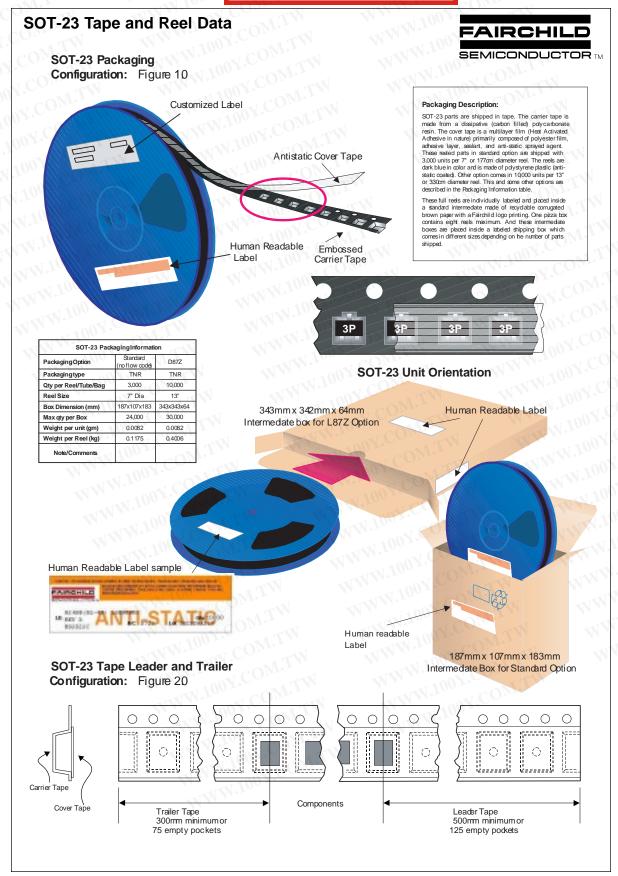




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



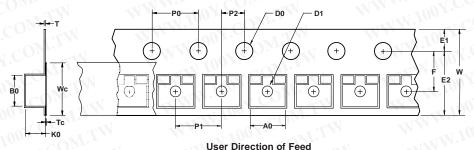


# SOT-23 Tape and Reel Data, continued

# **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0

**SOT-23** (8mm)



.10	$CO_{M}$		KI.				V.C	712	TW			N 41.	coo'
					Di	mension	s are in r	nillimete	r				
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	КО	T	Wc

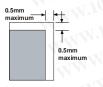
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



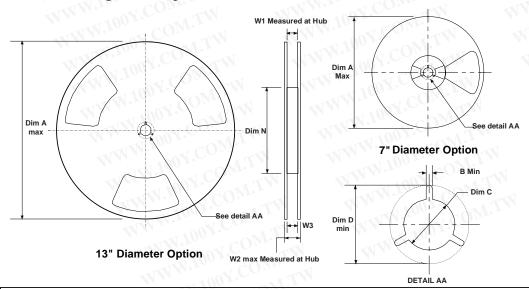
Sketch B (Top View)
Component Rotation



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Sketch C (Top View)
Component lateral movement

## SOT-23 Reel Configuration: Figure 4.0

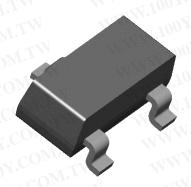


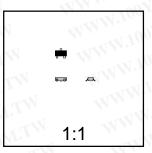
	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	

# **SOT-23 Package Dimensions**



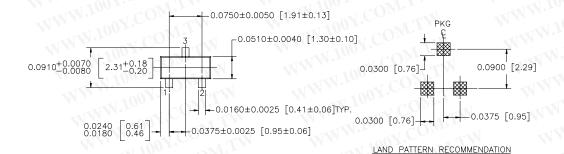
# SOT-23 (FS PKG Code 49)

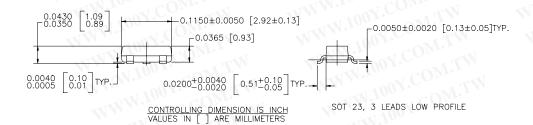




Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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